

MiniSKiiP[®] 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKIIP 36NAB126V10

Features

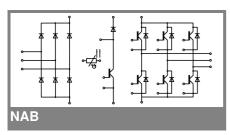
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 36 kVA
- Typical motor power 18,5 kW

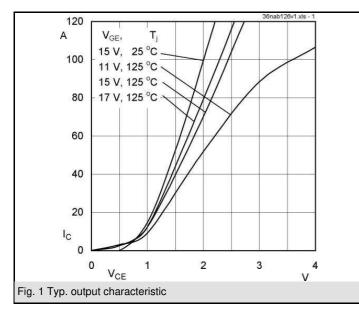
Remarks

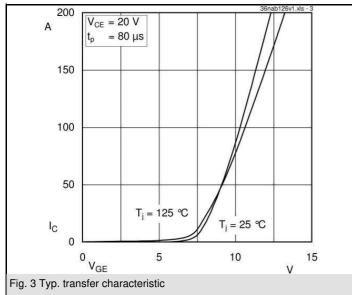
V_{CEsat}, V_F = chip level value

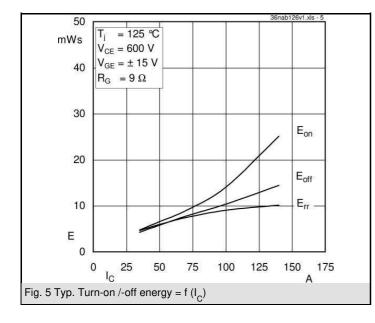


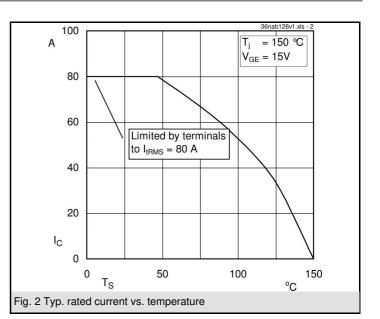
Absolute Maximum Ratings		T_s = 25 °C, unless otherwise specified						
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		1200	V					
I _C	T _s = 25 (70) °C	88 (66)	Α					
I _{CRM}		140	А					
V _{GES}		± 20	V					
Т _ј		- 40 + 150	°C					
Diode - Inverter, Chopper								
I _F	T _s = 25 (70) °C	91 (68)	А					
I _{FRM}		140	А					
Т _ј		- 40 + 150	°C					
Diode - Rectifier								
V _{RRM}		1600	V					
I _F	T _s = 70 °C	67	А					
I _{FSM}	t _p = 10 ms, sin 180 °, T _i = 25 °C	850	А					
i²t	t _p = 10 ms, sin 180 °, T _i = 25 °C	3600	A²s					
Т _ј		- 40 + 150	°C					
Module								
I _{tRMS}	per power terminal (20 A / spring)	80	А					
T _{stg}		- 40 + 125	°C					
V _{isol}	AC, 1 min.	2500	V					

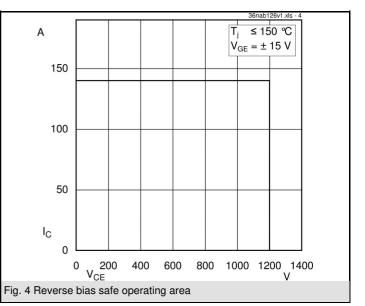
Characte	ristics	T _s = 25 °C,	$_{\rm s}$ = 25 °C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CEsat}	I _{Cnom} = 70 A, T _j = 25 (125) °C		1,7 (2)	2,1 (2,4)	V				
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 3 \text{ mA}$	5	5,8	6,5	V				
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V				
r _T	T _j = 25 (125) °C		10 (16)	13 (19)	mΩ				
C _{ies}	$V_{CE} = 25 \text{ V}, \text{ V}_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		4,8		nF				
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1		nF nF				
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,6						
R _{th(j-s)}	per IGBT		0,5		K/W				
t _{d(on)}	under following conditions		80		ns				
t,	V_{CC} = 600 V, V_{GE} = ± 15 V		25						
t _{d(off)}	I _{Cnom} = 70 A, T _j = 125°C		390		ns				
t _f	$R_{Gon} = R_{Goff} = 9 \Omega$		90		ns				
E _{on}	inductive load		9		mJ				
E _{off}			7,7		mJ				
Diode - In	verter, Chopper								
V _F = V _{EC}	I _{Fnom} = 70 A, T _i = 25 (125) °C		1,5 (1,5)	1,7 (1,7)	V				
V _(TO)	T _i = 25 (125) °C		1 (0,8)	1,1 (0,9)	V				
r _T	T _i = 25 (125) °C		7,1 (10)	8,6 (11)	mΩ				
R _{th(j-s)}	per diode		0,7		K/W				
I _{RRM}	under following conditions		77		Α				
Q _{rr}	I _{Fnom} = 70 A, V _R = 600 V		18		μC				
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		7,5		mJ				
	di _F /dt = 2000 A/µs								
Diode - R	ectifier	•							
V _F	I _{Fnom} = 40 A, T _i = 25 °C		1,1		V				
V _(TO)	T _i = 125 °C		0,8						
r _T	T _i = 125 °C		9						
$R_{th(j-s)}$	per diode		0,85		K/W				
	ure Sensor								
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω				
Mechanical Data									
w		1	95		g				
M _s	Mounting torque	2		2,5	Nm				

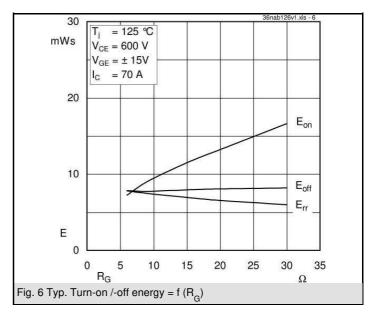




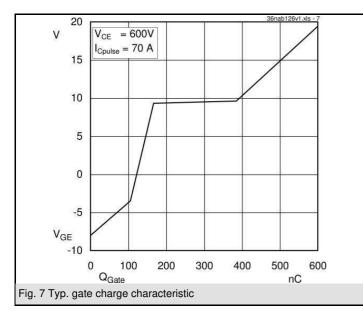


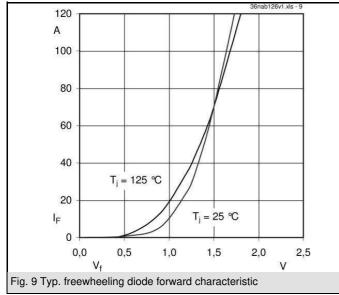


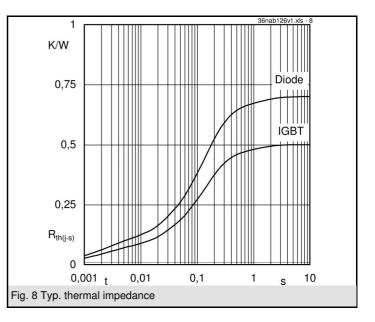


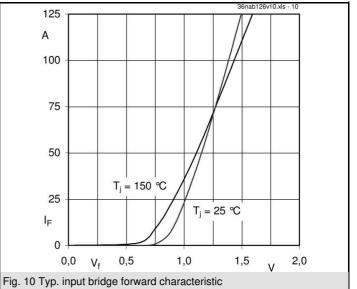


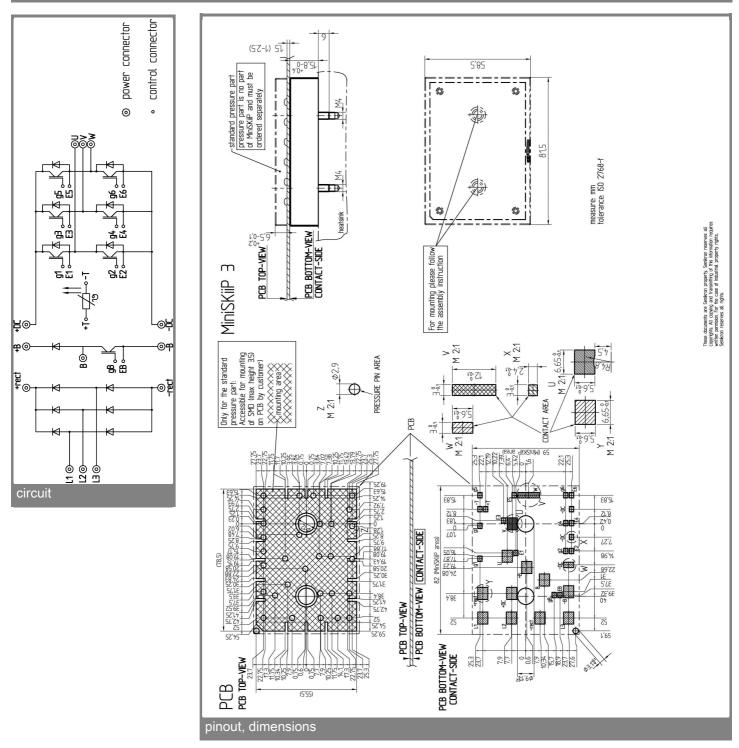
27-01-2010 LAN











This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.